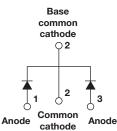
VS-HFA08TA60CSPbF

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 4 A



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PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
I _{F(AV)}	8 A							
V _R	600 V							
V _F at I _F	2.2 V							
t _{rr} (typ.)	17 ns							
T _J max.	150 °C							
Diode variation	Common cathode							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA08TA60CSPbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the VS-HFA08TA60CSPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current $\left(I_{\text{RRM}}\right)$ and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TA60CSPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Cathode to anode voltage	V _R		600	V						
Maximum continuous forward current	I_	T _C = 100 °C	4							
per device	IF		8	А						
Single pulse forward current	I _{FSM}		25	A						
Maximum repetitive forward current	I _{FRM}		16							
Maximum power dissipation	PD	T _C = 25 °C	25	W						
Maximum power dissipation	гD	T _C = 100 °C	10	vv						
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C						

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
Maximum forward voltage	V _{FM}	I _F = 4.0 A		-	1.5	1.8			
		I _F = 8.0 A	See fig. 1	-	1.8	2.2			
		I _F = 4.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse	I _{RM}	V _R = V _R rated	See fig. 0	-	0.17	3.0	μA		
leakage current		$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	44	300			
Junction capacitance	CT	V _R = 200 V See fig. 3		-	4.0	8.0	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	ackage body	-	8.0	-	nH		

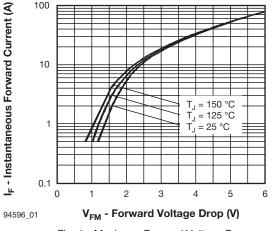
DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time See fig. 5, 6 and 16	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ J}$	Α/μs, V _R = 30 V	-	17	-			
	t _{rr1}	T _J = 25 °C		-	28	42	ns		
	t _{rr2}	T _J = 125 °C	I _F = 4.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	38	57			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	2.9	5.2	A		
See fig. 7 and 8	I _{RRM2}	T _J = 125 °C		-	3.7	6.7			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	40	60			
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C	VR - 200 V	-	70	105	no		
Peak rate of fall of recovery current during t _h	dl _{(rec)M} /dt1	T _J = 25 °C		-	280	-	A/µs		
See fig. 11 and 12	dl _{(rec)M} /dt2	T _J = 125 °C		-	235	-	Λµs		

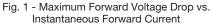
THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	- r\/ vv			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style D ² PAK		HFA08TA60CS					

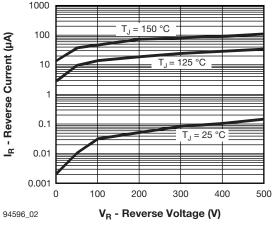


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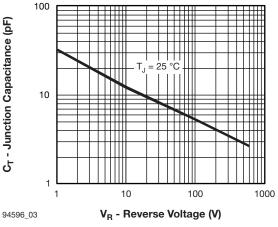
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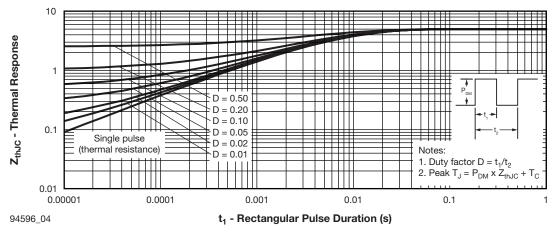


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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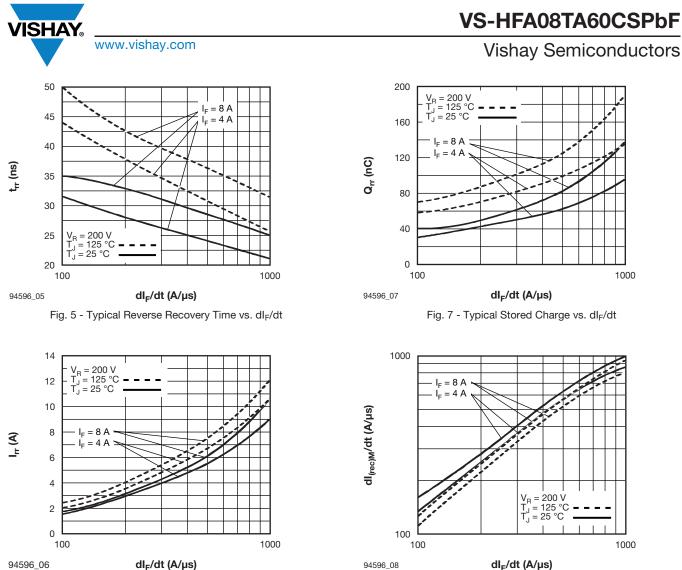




Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt





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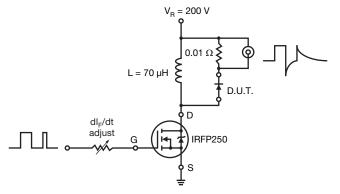
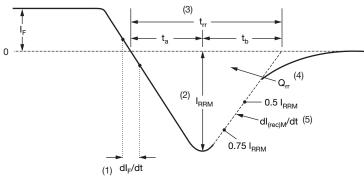


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (4) ${\rm Q}_{\rm rr}$ area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) $dI_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	08	ТА	60	С	S	TRL	PbF
	1	2	3	4	5	6	7	8	9	10
	 Vishay Semiconductors product HEXFRED[®] family Process designator: A = Electron irradiated Current rating (08 = 8 A) Package outline (TA = TO-220, 3 leads) Voltage rating (60 = 600 V) Circuit configuration (C = Common cathode) 									
	8 · 9 ·	• N • TI • TI • TI	RR = Ta bF = Lea		reel (rig free, for	ht orien tube pa	ted) ackageo			

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA08TA60CSPBF	50	1000	Antistatic plastic tube							
VS-HFA08TA60CSTRRP	800	800	13" diameter reel							
VS-HFA08TA60CSTRLP	800	800	13" diameter reel							

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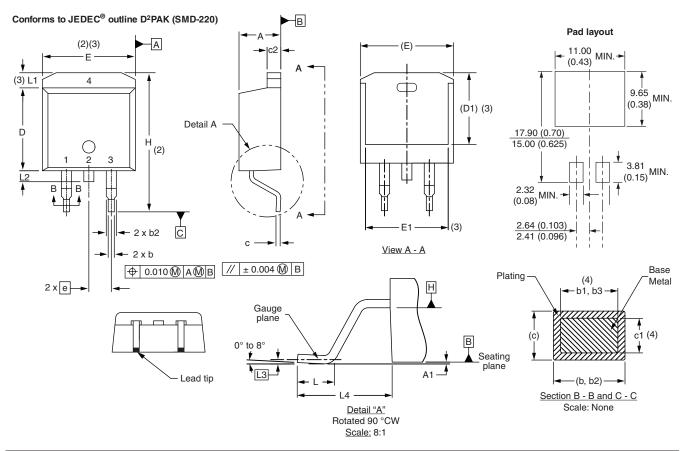
Outline Dimensions



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3 0.25 BSC		0.010 BSC			
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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